

WHAT IS CLAIMED IS:

1 1. A semiconductor integrated circuit device comprising:
2 a trench formed in a semiconductor substrate and defining active regions and
3 dummy regions;
4 an element isolation insulating film buried in said trench such that said
5 element isolation insulating film serves as an element isolation region;
6 an interlayer insulating film covering said substrate and said dummy regions
7 and including an insulating film planarized; and
8 external terminals formed over said interlayer insulating film such that said
9 dummy regions are formed under said external terminals.

1 2. A semiconductor integrated circuit device according to claim 1, wherein a
2 length of said dummy region is shorter than a distance between said external
3 terminals.

1 3. A semiconductor integrated circuit device comprising:
2 a trench formed in a semiconductor substrate and defining active regions and
3 dummy regions;
4 an element isolation insulating film buried in said trench such that said
5 element isolation insulating film serves as an element isolation region;
6 an interlayer insulating film covering said substrate and said dummy regions;
7 and
8 an external terminal formed over said interlayer insulating film such that said
9 dummy regions are formed under said external dummy regions and such that
10 dummy interconnections each comprised of a same layer as external terminal are
11 not formed at said scribing area.

1 4. A semiconductor integrated circuit device comprising:
2 a trench formed in a semiconductor substrate and defining active regions and

3 dummy regions;
4 an element isolation insulating film buried in said trench such that said
5 element isolation insulating film serves as an element isolation region;
6 an interlayer insulating film covering said substrate and said dummy regions;
7 external terminals formed over said interlayer insulating film such that said
8 dummy regions are formed under said external terminals;
9 interconnections each comprised of a same layer as external terminal and
10 formed over said interlayer insulating film; and
11 dummy interconnections each comprised of a same layer as external terminal
12 and spaced from said interconnections.

1 5. A semiconductor integrated circuit device according to claim 4, wherein a
2 length of said interconnection is shorter than a distance between said external
3 terminals.

1 6. A semiconductor integrated circuit device comprising:
2 a trench formed in a semiconductor substrate and defining active regions and
3 dummy regions;
4 an element isolation insulating film buried in said trench such that said
5 element isolation insulating film serves as an element isolation region;
6 gate electrodes formed over said active regions and serving as gate
7 electrodes of MISFET type elements; and
8 dummy patterns each comprised of a same layer as said gate electrodes and
9 formed in a region spaced from said gate electrodes and a marker portion for
10 photolithography.